Supplementary Information for

Alleviating the crosstalk effect via a finemoulded light-blocking matrix for colourconverted micro-LED display with a 122% NTSC gamut

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Fig. S1 Schematic diagram of top-emitting micro-LED array without LBM.



Fig. S2 Simulation model of top-emitting structure (a) without and (b) with light-blocking matrix

(LBM).



Fig. S3 Schematic of the pixel design for the target display panel. The elliptical circles drawn here are to indicate the bank design of the CCL plate.



Fig. S4 (a) Schematic and (b) image of the metal mask design for MSP approach. It contains approximate rings (see the red rectangle in Fig. S4a) where the metal blocks corresponding to the micro-LED positions were connected with narrow metal stripes. Based this design and the fluid characteristics of pastes, it was anticipated to encircle the micro-LED chips with black paste.



Fig. S5 (a) Transmittance spectra of black LBM films with different thickness and (b) photographs of LBM films stacked on top of blue "O" patterns.



Fig. S6 Characteristics of blue micro-LED backlight. Photographs of a blue micro-LED backlight molded with black LBM under (a) off and (b) on states. (c) Cross-sectional microscopic images of the micro-LED chips filled with black LBM.



Fig. S7 (a) External photograph and (b) internal schematic view of the plasma etching equipment (Boffotto M01S, Boffotto Co., Ltd., Zhuhai, China).



Fig. S8 Processes to manufacture top-emitting active matrix color-converted micro-LED display.



Fig. S9 Photographs of (a) red and (b) green CdSe patterns under excitation by UV light. (c) Red, green and blue pixel patterns illuminated by blue backlight.

| Simulation Component | Value (µm) | Crosstalk Ratio |
|---|-------------------------------|-----------------|
| | 166.6 (Pixel Pitch: 500μm) | 19.9% |
| Micro-LED Pitch | 300 | 4.53% |
| (Gap: 10 μm; Black Bank CD: 80 μm) | 350 | 3.33% |
| | 400 | 2.48% |
| | 450 | 1.3% |
| | 20 | 1.9% |
| Black Bank Critical Dimension (CD) | 60 | 1.6% |
| (Micro-LED Pitch: 450 μm; Gap: 10 μm) | 80 | 1.3% |
| | 100 | 1.1% |
| | 20 | 1.7% |
| Gap | 10 | 1.3% |
| (Micro-LED Pitch: 450 µm; Black Bank CD: 80 µm) | 5 | 1.1% |
| | 0 | 1.0% |

 Table S1 Simulation results of top-emitting architecture without LBM.

| Tr% of LBM | Red | Green | Blue | XT% | Gamut (NTSC) |
|---------------|------------------|------------------|--------|-------|-----------------|
| 0 | 628 nm | 532 nm | 452 nm | 0 | 128.0% |
| 1% | 628 nm | 532 nm | 452 nm | 0. 2% | 126% |
| 10% | 628 nm 452 nm | 532 nm | 452 nm | 4.1% | 112.5% |
| 20% | 628 nm 452 nm | 532 nm 452 nm | 452 nm | 7.3% | 85.3% |
| 30% | 628 nm 452 nm | 532 nm 452 nm | 452 nm | 9.6% | 63.2% |
| 50% | 628 nm 452 nm | 532 nm 452 nm | 452 nm | 15.8% | 32.3% |

Table S2 Simulation results of top-emitting architecture with LBM of different transmittance.

| Component | Emission Peak | CIE Coordinates | FWHM |
|-----------------------------|---------------|------------------|------|
| Component | (nm) | (x, y) | (nm) |
| Blue Micro-LED | 452 | (0.1494, 0.0243) | 19 |
| Blue Micro-LED + Red CdSe | 628 | (0.6732, 0.3052) | 27 |
| Blue Micro-LED + Green CdSe | 532 | (0.1567, 0.7671) | 22 |
| Blue Micro-LED | 462 | (0.1432, 0.0396) | 15 |
| Red Micro-LED | 619 | (0.6898, 0.3103) | 14 |
| Green Micro-LED | 541 | (0.2469, 0.7161) | 25 |

 Table S3 Photoconversion performance and optical characteristics.